

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_M881-CDMA BC0-RC3 SO55-777CH

DUT: M881; Type: cdma2000 Digital Mobile Phone; Asura; Serial: SAR1

Communication System: HW-CDMA 2000; Frequency: 848.31 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1); Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 47.62 V/m; Power Drift = -0.00 dB

PMF = 1.050 is applied.

E-field emissions = 40.51 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

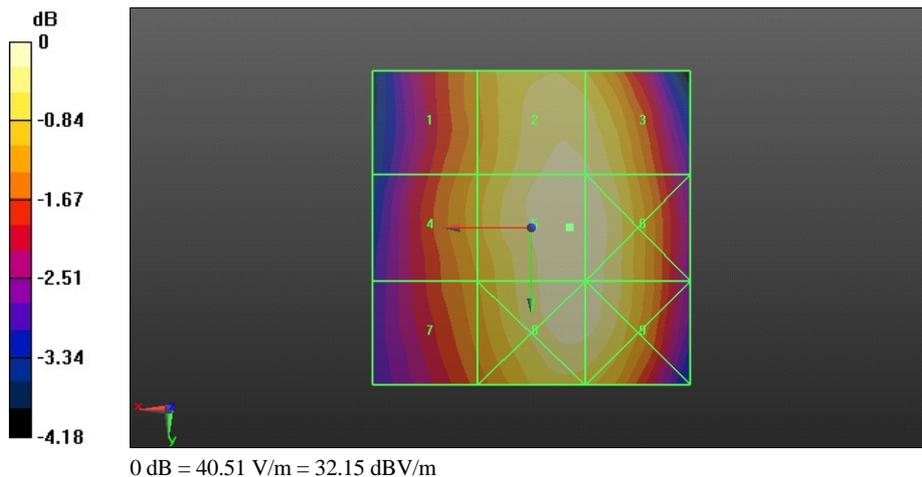
Grid 1 M4 35.89 V/m	Grid 2 M4 39.73 V/m	Grid 3 M4 39.52 V/m
Grid 4 M4 36.49 V/m	Grid 5 M4 40.51 V/m	Grid 6 M4 40.41 V/m
Grid 7 M4 35.57 V/m	Grid 8 M4 40.25 V/m	Grid 9 M4 40.07 V/m

Cursor:

Total = 40.51 V/m

E Category: M4

Location: -6, 0, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_M881-CDMA BC0-RC3 SO55-384CH

DUT: M881; Type: cdma2000 Digital Mobile Phone; Asura; Serial: SAR1

Communication System: HW-CDMA 2000; Frequency: 836.52 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 51.45 V/m; Power Drift = -0.11 dB

PMF = 1.050 is applied.

E-field emissions = 43.38 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

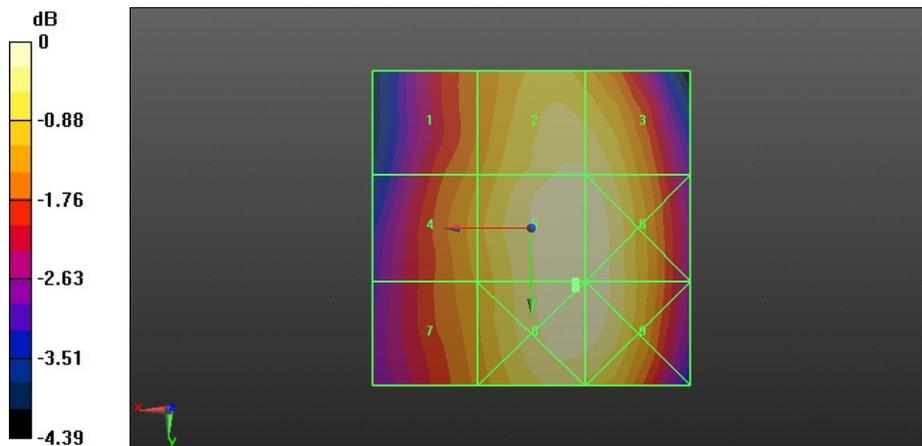
Grid 1 M4 37.65 V/m	Grid 2 M4 42.28 V/m	Grid 3 M4 42.19 V/m
Grid 4 M4 38.73 V/m	Grid 5 M4 43.38 V/m	Grid 6 M4 43.29 V/m
Grid 7 M4 38.13 V/m	Grid 8 M4 43.40 V/m	Grid 9 M4 43.31 V/m

Cursor:

Total = 43.40 V/m

E Category: M4

Location: -7, 9.5, 8.7 mm



0 dB = 43.40 V/m = 32.75 dBV/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_M881-CDMA BC0-RC3 SO55-1013CH

DUT: M881; Type: cdma2000 Digital Mobile Phone; Asura; Serial: SAR1

Communication System: HW-CDMA 2000; Frequency: 824.7 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1); Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 50.98 V/m; Power Drift = -0.09 dB

PMF = 1.050 is applied.

E-field emissions = 42.68 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

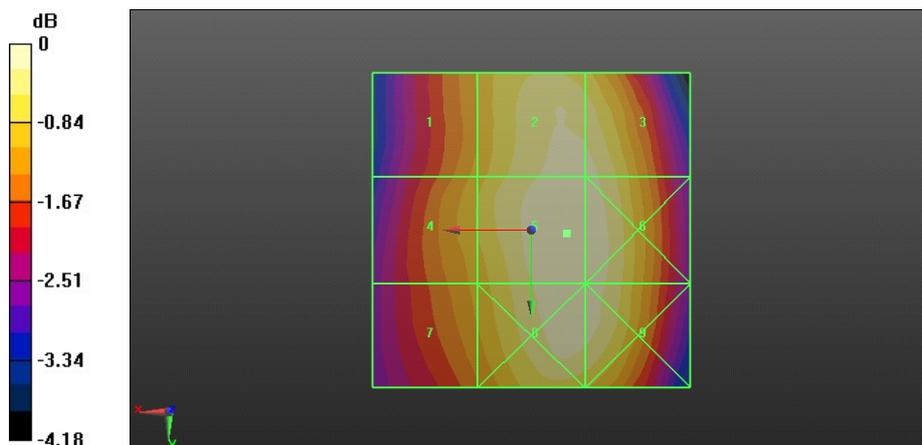
Grid 1 M4 38.13 V/m	Grid 2 M4 42.06 V/m	Grid 3 M4 41.95 V/m
Grid 4 M4 38.90 V/m	Grid 5 M4 42.68 V/m	Grid 6 M4 42.55 V/m
Grid 7 M4 38.04 V/m	Grid 8 M4 42.45 V/m	Grid 9 M4 42.28 V/m

Cursor:

Total = 42.68 V/m

E Category: M4

Location: -5.5, 0.5, 8.7 mm



0 dB = 42.68 V/m = 32.61 dBV/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_M881-CDMA BC0-RC3 SO55-384CH with battery 2#

DUT: M881; Type: cdma2000 Digital Mobile Phone; Asura; Serial: SAR1

Communication System: HW-CDMA 2000; Frequency: 836.52 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 49.77 V/m; Power Drift = 0.07 dB

PMF = 1.050 is applied.

E-field emissions = 42.35 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

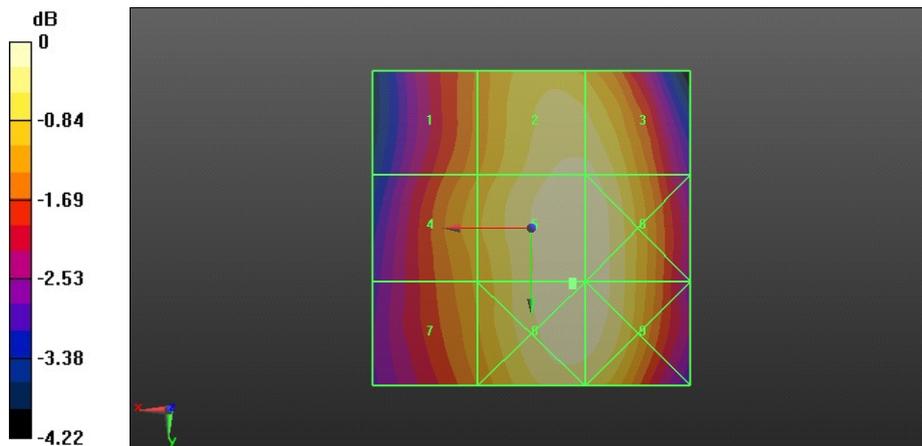
Grid 1 M4 37.12 V/m	Grid 2 M4 41.47 V/m	Grid 3 M4 41.43 V/m
Grid 4 M4 38.24 V/m	Grid 5 M4 42.35 V/m	Grid 6 M4 42.25 V/m
Grid 7 M4 37.50 V/m	Grid 8 M4 42.35 V/m	Grid 9 M4 42.26 V/m

Cursor:

Total = 42.35 V/m

E Category: M4

Location: -6.5, 9, 8.7 mm



0 dB = 42.35 V/m = 32.54 dBV/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_M881-CDMA BC1-RC3 SO55-1175CH

DUT: M881; Type: cdma2000 Digital Mobile Phone; Asura; Serial: SAR1

Communication System: HW-CDMA 2000; Frequency: 1908.75 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 25.96 V/m; Power Drift = -0.10 dB

PMF = 1.020 is applied.

E-field emissions = 30.13 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

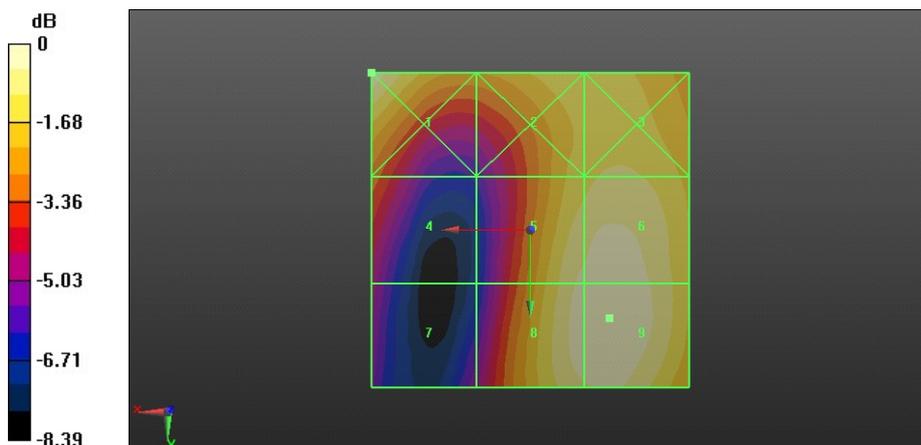
Grid 1 M4 30.24 V/m	Grid 2 M4 26.16 V/m	Grid 3 M4 26.89 V/m
Grid 4 M4 21.51 V/m	Grid 5 M4 28.92 V/m	Grid 6 M4 29.77 V/m
Grid 7 M4 17.77 V/m	Grid 8 M4 29.38 V/m	Grid 9 M4 30.13 V/m

Cursor:

Total = 30.24 V/m

E Category: M4

Location: 25, -25, 8.7 mm



0 dB = 30.24 V/m = 29.61 dBV/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_M881-CDMA BC1-RC3 SO55-600CH

DUT: M881; Type: cdma2000 Digital Mobile Phone; Asura; Serial: SAR1

Communication System: HW-CDMA 2000; Frequency: 1880 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 22.46 V/m; Power Drift = 0.11 dB

PMF = 1.020 is applied.

E-field emissions = 29.86 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

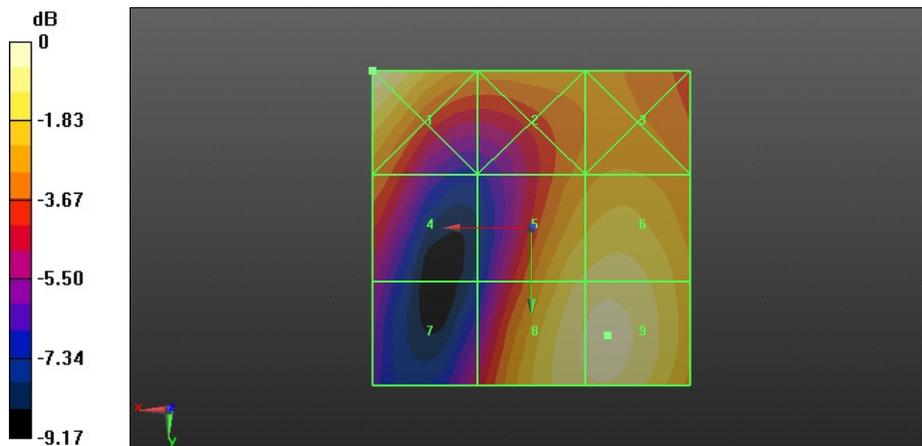
Grid 1 M4 31.27 V/m	Grid 2 M4 23.17 V/m	Grid 3 M4 23.87 V/m
Grid 4 M4 22.52 V/m	Grid 5 M4 27.68 V/m	Grid 6 M4 28.46 V/m
Grid 7 M4 18.08 V/m	Grid 8 M4 29.36 V/m	Grid 9 M4 29.86 V/m

Cursor:

Total = 31.27 V/m

E Category: M4

Location: 25, -25, 8.7 mm



0 dB = 31.27 V/m = 29.90 dBV/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_M881-CDMA BC1-RC3 SO55-25CH

DUT: M881; Type: cdma2000 Digital Mobile Phone; Asura; Serial: SAR1

Communication System: HW-CDMA 2000; Frequency: 1851.25 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1); Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 21.33 V/m; Power Drift = 0.06 dB

PMF = 1.020 is applied.

E-field emissions = 28.72 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

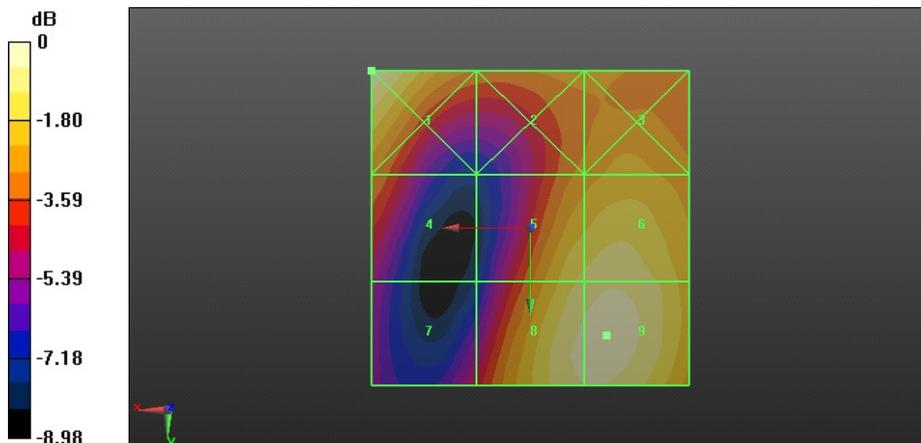
Grid 1 M4 29.76 V/m	Grid 2 M4 21.71 V/m	Grid 3 M4 23.37 V/m
Grid 4 M4 21.41 V/m	Grid 5 M4 26.52 V/m	Grid 6 M4 27.52 V/m
Grid 7 M4 17.66 V/m	Grid 8 M4 28.21 V/m	Grid 9 M4 28.72 V/m

Cursor:

Total = 29.76 V/m

E Category: M4

Location: 25, -25, 8.7 mm



0 dB = 29.76 V/m = 29.47 dBV/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_M881-CDMA BC1-RC3 SO55-1175CH with battery 2#

DUT: M881; Type: cdma2000 Digital Mobile Phone; Asura; Serial: SAR1

Communication System: HW-CDMA 2000; Frequency: 1908.75 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 26.53 V/m; Power Drift = -0.12 dB

PMF = 1.020 is applied.

E-field emissions = 30.92 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

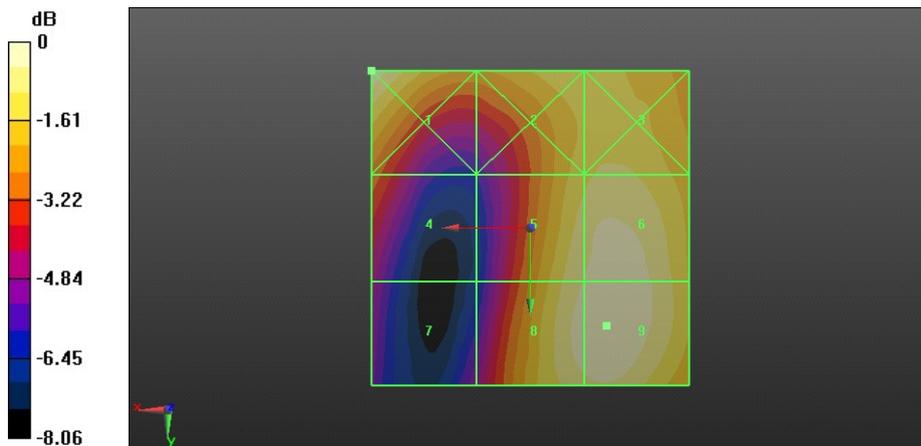
Grid 1 M4 31.34 V/m	Grid 2 M4 27.23 V/m	Grid 3 M4 28.08 V/m
Grid 4 M4 22.70 V/m	Grid 5 M4 29.59 V/m	Grid 6 M4 30.62 V/m
Grid 7 M4 18.54 V/m	Grid 8 M4 30.29 V/m	Grid 9 M4 30.92 V/m

Cursor:

Total = 31.34 V/m

E Category: M4

Location: 25, -25, 8.7 mm



0 dB = 31.34 V/m = 29.92 dBV/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_M881-CDMA BC0-RC3 SO55-777CH

DUT: M881; Type: cdma2000 Digital Mobile Phone; Asura; Serial: SAR1

Communication System: HW-CDMA 2000; Frequency: 848.31 MHz; Duty Cycle: 1:1
 Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$
 Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

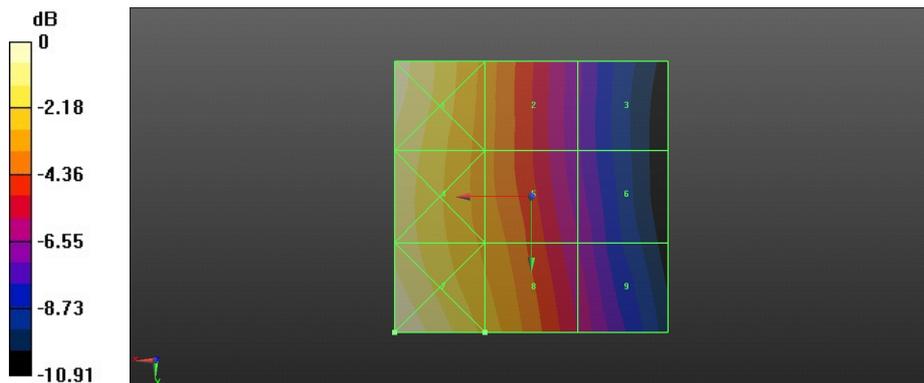
Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm
 Reference Value = 0.05300 A/m; Power Drift = 0.18 dB
 PMF = 0.9900 is applied.
 H-field emissions = 0.06719 A/m
Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

Grid 1 M4 0.085 A/m	Grid 2 M4 0.062 A/m	Grid 3 M4 0.039 A/m
Grid 4 M4 0.080 A/m	Grid 5 M4 0.062 A/m	Grid 6 M4 0.042 A/m
Grid 7 M4 0.088 A/m	Grid 8 M4 0.067 A/m	Grid 9 M4 0.045 A/m

Cursor:
 Total = 0.08836 A/m
 H Category: M4
 Location: 25, 25, 8.7 mm



0 dB = 0.08836 A/m = -21.07 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_M881-CDMA BC0-RC3 SO55-384CH

DUT: M881; Type: cdma2000 Digital Mobile Phone; Asura; Serial: SAR1

Communication System: HW-CDMA 2000; Frequency: 836.52 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.05400 A/m; Power Drift = 0.05 dB

PMF = 0.9900 is applied.

H-field emissions = 0.06877 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

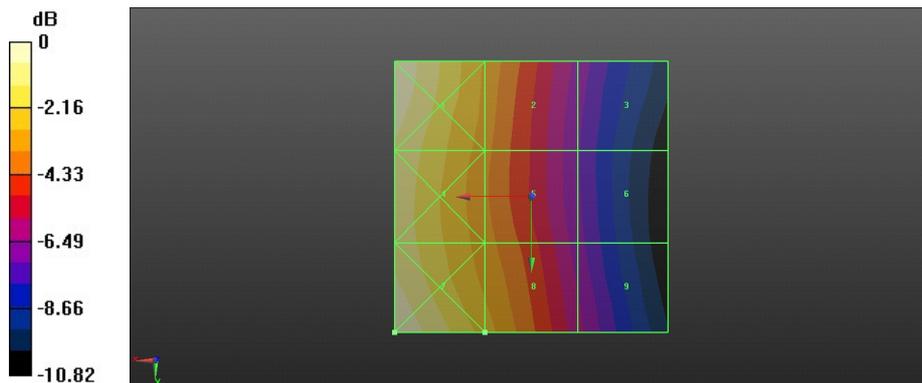
Grid 1 M4 0.090 A/m	Grid 2 M4 0.065 A/m	Grid 3 M4 0.042 A/m
Grid 4 M4 0.084 A/m	Grid 5 M4 0.063 A/m	Grid 6 M4 0.042 A/m
Grid 7 M4 0.092 A/m	Grid 8 M4 0.069 A/m	Grid 9 M4 0.045 A/m

Cursor:

Total = 0.09164 A/m

H Category: M4

Location: 25, 25, 8.7 mm



0 dB = 0.09164 A/m = -20.76 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_M881-CDMA BC0-RC3 SO55-1013CH

DUT: M881; Type: cdma2000 Digital Mobile Phone; Asura; Serial: SAR1

Communication System: HW-CDMA 2000; Frequency: 824.7 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.05400 A/m; Power Drift = -0.02 dB

PMF = 0.9900 is applied.

H-field emissions = 0.06920 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

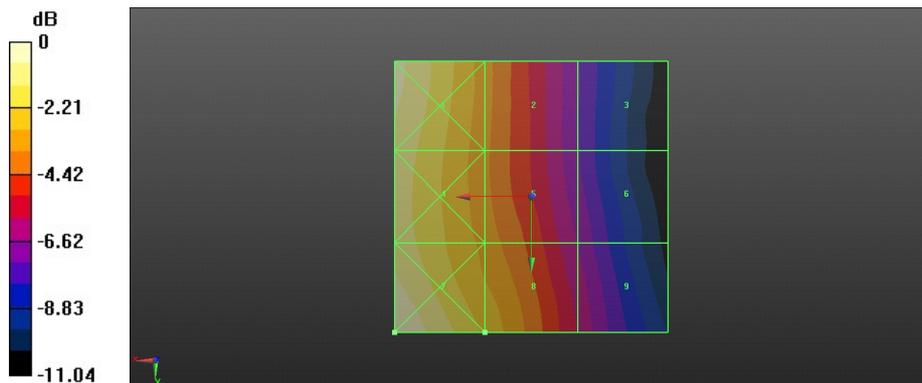
Grid 1 M4 0.086 A/m	Grid 2 M4 0.062 A/m	Grid 3 M4 0.039 A/m
Grid 4 M4 0.082 A/m	Grid 5 M4 0.063 A/m	Grid 6 M4 0.042 A/m
Grid 7 M4 0.091 A/m	Grid 8 M4 0.069 A/m	Grid 9 M4 0.046 A/m

Cursor:

Total = 0.09051 A/m

H Category: M4

Location: 25, 25, 8.7 mm



0 dB = 0.09051 A/m = -20.87 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_M881-CDMA BC0-RC3 SO55-384CH with battery 2#

DUT: M881; Type: cdma2000 Digital Mobile Phone; Asura; Serial: SAR1

Communication System: HW-CDMA 2000; Frequency: 836.52 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.05400 A/m; Power Drift = 0.02 dB

PMF = 0.9900 is applied.

H-field emissions = 0.06832 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

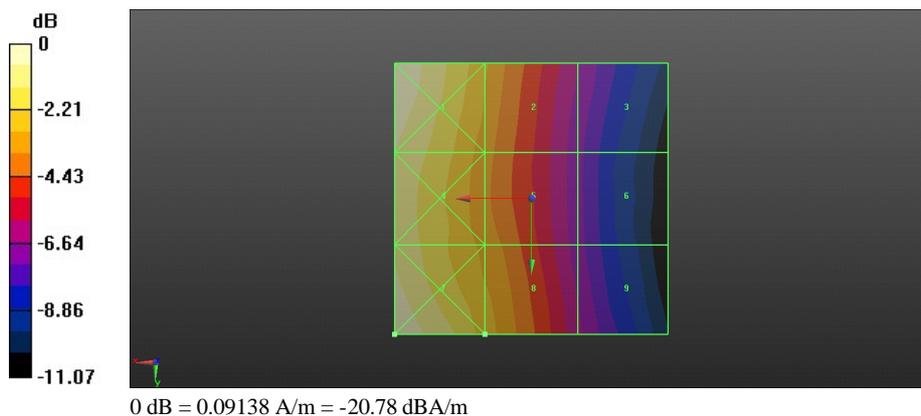
Grid 1 M4 0.090 A/m	Grid 2 M4 0.066 A/m	Grid 3 M4 0.043 A/m
Grid 4 M4 0.084 A/m	Grid 5 M4 0.063 A/m	Grid 6 M4 0.041 A/m
Grid 7 M4 0.091 A/m	Grid 8 M4 0.068 A/m	Grid 9 M4 0.044 A/m

Cursor:

Total = 0.09138 A/m

H Category: M4

Location: 25, 25, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_M881-CDMA BC1-RC3 SO55-1175CH

DUT: M881; Type: cdma2000 Digital Mobile Phone; Asura; Serial: SAR1

Communication System: HW-CDMA 2000; Frequency: 1908.75 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.08600 A/m; Power Drift = -0.11 dB

PMF = 0.9400 is applied.

H-field emissions = 0.08168 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

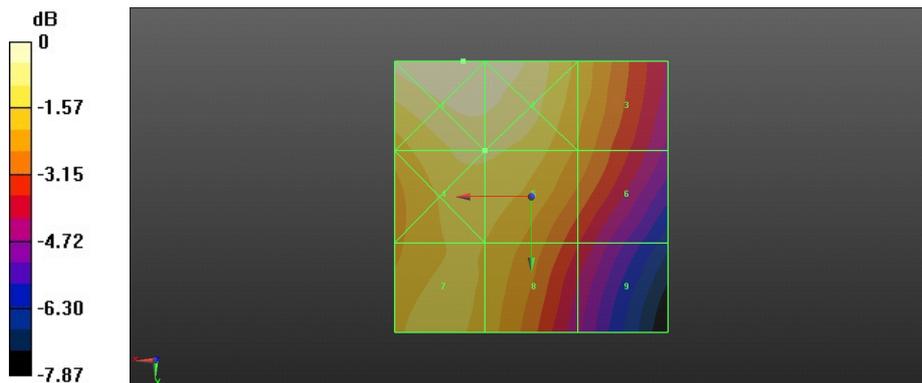
Grid 1 M4 0.091 A/m	Grid 2 M4 0.089 A/m	Grid 3 M4 0.074 A/m
Grid 4 M4 0.082 A/m	Grid 5 M4 0.082 A/m	Grid 6 M4 0.070 A/m
Grid 7 M4 0.077 A/m	Grid 8 M4 0.076 A/m	Grid 9 M4 0.060 A/m

Cursor:

Total = 0.09061 A/m

H Category: M4

Location: 12.5, -25, 8.7 mm



0 dB = 0.09061 A/m = -20.86 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_M881-CDMA BC1-RC3 SO55-600CH

DUT: M881; Type: cdma2000 Digital Mobile Phone; Asura; Serial: SAR1

Communication System: HW-CDMA 2000; Frequency: 1880 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.08400 A/m; Power Drift = -0.13 dB

PMF = 0.9400 is applied.

H-field emissions = 0.07634 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

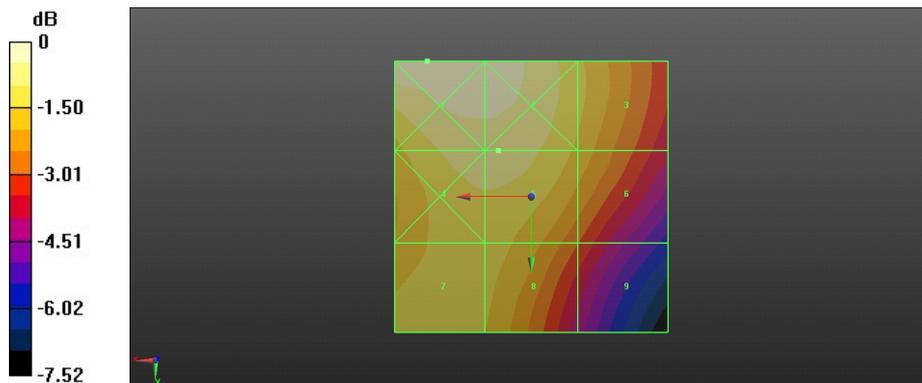
Grid 1 M4 0.083 A/m	Grid 2 M4 0.081 A/m	Grid 3 M4 0.071 A/m
Grid 4 M4 0.076 A/m	Grid 5 M4 0.076 A/m	Grid 6 M4 0.068 A/m
Grid 7 M4 0.074 A/m	Grid 8 M4 0.072 A/m	Grid 9 M4 0.059 A/m

Cursor:

Total = 0.08261 A/m

H Category: M4

Location: 19, -25, 8.7 mm



0 dB = 0.08261 A/m = -21.66 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_M881-CDMA BC1-RC3 SO55-25CH

DUT: M881; Type: cdma2000 Digital Mobile Phone; Asura; Serial: SAR1

Communication System: HW-CDMA 2000; Frequency: 1851.25 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.07700 A/m; Power Drift = 0.01 dB

PMF = 0.9400 is applied.

H-field emissions = 0.07247 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

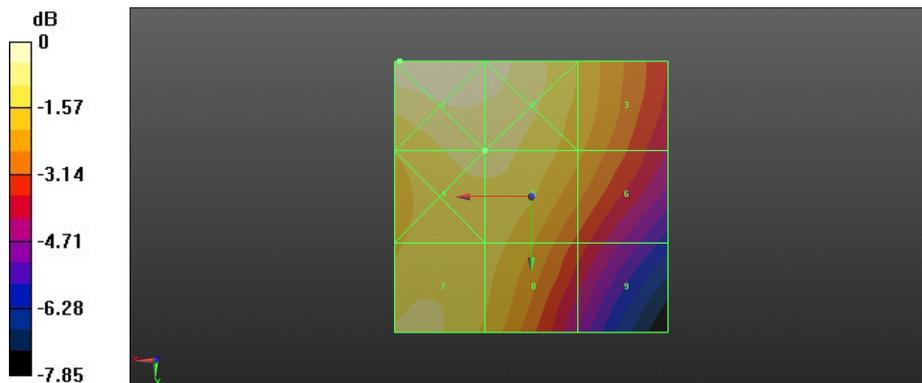
Grid 1 M4 0.080 A/m	Grid 2 M4 0.078 A/m	Grid 3 M4 0.067 A/m
Grid 4 M4 0.072 A/m	Grid 5 M4 0.072 A/m	Grid 6 M4 0.064 A/m
Grid 7 M4 0.072 A/m	Grid 8 M4 0.069 A/m	Grid 9 M4 0.055 A/m

Cursor:

Total = 0.08015 A/m

H Category: M4

Location: 24, -25, 8.7 mm



0 dB = 0.08015 A/m = -21.92 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_M881-CDMA BC1-RC3 SO55-1175CH with battery 2#

DUT: M881; Type: cdma2000 Digital Mobile Phone; Asura; Serial: SAR1

Communication System: HW-CDMA 2000; Frequency: 1908.75 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.08700 A/m; Power Drift = -0.19 dB

PMF = 0.9400 is applied.

H-field emissions = 0.08180 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

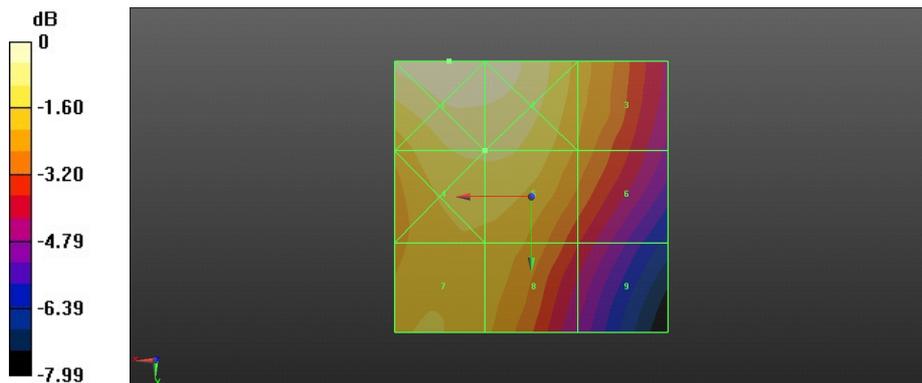
Grid 1 M4 0.091 A/m	Grid 2 M4 0.089 A/m	Grid 3 M4 0.074 A/m
Grid 4 M4 0.082 A/m	Grid 5 M4 0.082 A/m	Grid 6 M4 0.070 A/m
Grid 7 M4 0.076 A/m	Grid 8 M4 0.075 A/m	Grid 9 M4 0.060 A/m

Cursor:

Total = 0.09106 A/m

H Category: M4

Location: 15, -25, 8.7 mm



0 dB = 0.09106 A/m = -20.81 dBA/m